PCN Number:			PCN20141121002 PCN Date: 11/2						1/22	/14							
Tit	Qualification of Additional Fab Site (UMC/DP1DM5) and Assembly Site (Amkor Philippines) for Select Devices																
Cu	stom	er Contact:	PCN Manager		Pho	one:	+1(2	-1(214)480-6037			Dept:		Quality Services				
Proposed 1 st Ship Da		ite:	02/23/2015	E	Estim	ated	Sampl	e A	vaila	ability: Provided u			on				
Ch	Change Type:																
\boxtimes	Asse	mbly Site		Assembly	Proc	cess				Asse	embly M	ateri	als	S			
	Desi			Electrical							nanical	_	ific	cat	tion		
Щ	Test			Packing/S				g			Proces						
		er Bump Site	Ļ	Wafer Bur					_		er Bum						
\boxtimes	Wafe	er Fab Site		Wafer Fab						Wafe	er Fab F	roce	SS	i			
				Part numb													
		ion of Chang			PCI	N De	tails	<u> </u>									
for DP: The The	Texas Instruments is pleased to announce the qualification of an additional Fab and Assembly site for the devices listed in the Product Affected Section. For the devices listed in Group 1, UMC and DP1DM5 will be qualified as an additional fab site and Amkor Philippines as a new Assembly site. The devices listed in Group 2 will have only an additional Fab sites qualified (UMC and DP1DM5). There are no differences in wafer diameter or fab processes between current and new fab sites. There is no material differences between devices assembled at the 2 sites in either qualification group.																
		for Change:															
		y of Supply				_									_	_	
An	ticipa	ted impact o	n Fit	t, Form, Fund	ction	ı, Qua	ality o	r Relia	abi	lity (positiv	e / r	1e	ga	tive	e):	
Noi	ne																
			ident	tification res	ultir	ng fro	m th	is PCN	:								
As	sseml	oly Site															
PS	SI		Α	ssembly Site	Origi	in (22	2L)			AS	O: PAC						
Aı	mkor	Philippines	As	sembly Site	Orig	jin (2	2L)			AS	O: AP3						
	i p Sit e urrent	e:															
Cł	nip Sit	е	Chi	Chip site code (20L) Chip country code (21L)													
CF	AB		CU	CU3 CHN													
M:	IHO8		МН	8			JI	PN									
Ne	ew .						· ·										
	nip Si	te	Chi	p site code (20 L)	С	hip co	un	try co	de (21	.L)					
DF	P1DM5		DM!	5			U	SA							\dashv		
UI	MC-F8	AB	UAE	3			Т	WN									
Sar	Sample product shipping label (not actual product label)																



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483\$I2 (P) (2P) REV: (V) 0033317 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS

PPT: 1750 LBL: 5A (L)TO:1750

Topside Device marking:

Assembly site code for PAC= E

Assembly site code for AP3 = 3

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Group 1 Devices (Assembly/Adding Amkor & Fab/Adding UMC-F8AB and DP1DM5):

CSD59972BQ5MC	CSD59974BQ5MC	CSD95372BQ5MC	CSD95378BQ5MC
CSD59973BQ5MC	CSD59974BQ5MCT	CSD95372BQ5MCT	CSD95378BQ5MCT
CSD59973BQ5MCT			

Group 2 Devices (Fab Only/Adding UMC-F8AB/DP1DM5):

CSD59962Q5M	CSD95372BQ5MT	CSD95373BQ5MT	CSD95378BQ5MT
CSD95372BQ5M	CSD95373BQ5M	CSD95378BQ5M	

Amkor Philippines Qualification Data:



5x6 QFN Q5MC Power Stage Qualification Summary at AMKOR-P3 NCH MOSFET – Gen 2.1 25-10

CSD9537	CSD95372BQ5MC Miho, CFAB and Amkor-P3 Qualification Test Summary							
Stress Conditions		Test Duration	Sample Size	Results				
HTS	150°C, unbiased Bake	nbiased Bake 1K hrs 3 lots x 77 units Pa		Pass				
Autoclave	121°C/100% RH 96 hrs 3 lots x 77 units		Pass					
Temp Cycle	-55°C to +125°C	1K cycles	3 lots x 77 units	Pass				
HTOL**	125°C/100% Rated Vin	1K hrs	3 lots x 77 units	Pass				
Intermittent Op Life	Delta Tj = 100°C 2 min on/3 min off	10K cycles	3 lot x 77 units	Pass				
Biased HAST	130°C/85% RH 80% Rated Vds	96 hrs	3 lots x 77 units	Pass				
HTRB*	150°C/80% Rated Vds	1K hrs	3 lots x 77 units	Pass				
HTGB* 150°C/80% Rated Vgs		1K hrs	3 lots x 77 units	Pass				

 $\ensuremath{\mathsf{MSL2}}$ preconditioning performed on devices prior to Autoclave, biased HAST & Temp Cycle stresses

- Bake: 24 hours @ 125°C
- Damp Heat: 168 hours @ 85°C/60% RH (Level 2)
- 3X reflow + flux + rinse, 260°C Pb free reflow temp

Assembly Qual Lot Matrix:

REBUILD

ILN	O-view	Batch	Lot 1	Lot 2	Lot 3
ILIN	Device	batteri			
Di- 4		3344013CU3	#12		#11
Die 1	G5N353045AU	3276001CU3		#2	
Die 2	G5N36333SB1	3276003CU3	#1	#2	#1
Die 3	LCSD32000G1	4010917PHX	#21	#21	#21

^{*} HTRB & HTGB were performed on the CSD86360Q5D product qualification

UMC Fab Qualification Data:

^{**} HTOL was performed on the CSD95372AQ5M product qualification

UMC Fab 8E Qualification Summary NCH 25N16 & 30N10 MOSFET

CS	CSD16404Q5A & CSD17310Q5A Qualification Test Summary							
Stress Conditions		Test Duration	Sample Size	Results				
HTRB	HTRB 150°C/80% Rated Vds 1K hrs		3 lots x 77 units	Pass				
HTGB	HTGB 150°C/80% Rated Vgs		3 lots x 77 units	Pass				
ТНВ	THB 85°C/85%R.H./80% Rated Vds		3 lots x 77 units	Pass				
Autoclave	121C/100% RH	96 hrs	3 lots x 77 units	Pass				
Intermittent Op Life Delta Tj = 100°C 2 min on/2 min off		10K cycles	3 lots x 77 units	Pass				
Temp Cycle -40°C to 125°C		1K cycles	3 lots x 77 units	Pass				

DP1DM5 Fab Qualification Data:

DP1DM5 Fab Qualification Data:								
		ata: (Approved 2/						
	This qualification has been developed for the validation of this change. The							
qualification data will validate that the proposed change meets the applicable								
released technical specifications.								
Qualification Device: BQ24721RHB								
Wafer Fab Site: DMOS5 Wafer Fab Process: LBC7								
Qualification: Plan Test Results								
Reliability Test	Conditions			ample Si				
•	4700 (400)		Lot#1	Lot#2	Lot#3			
**High Temp. Storage	170C (420hrs)		77/0	77/0	77/0			
**Autoclave 121C	240 Hrs		77/0	77/0	77/0			
**Temp Cycle	-65C/+150C (1	000 Cyc)	77/0	77/0	77/0			
**Thermal Shock	-65C/+150C (1	77/0	77/0	77/0				
ESD HBM +/- 2000\			3/0	3/0	3/0			
ESD CDM	+/- 500V		3/0	3/0	3/0			
ESD MM	+/- 100V		3/0	3/0	3/0			
Latch-up	100mA		5/0	5/0	5/0			
Electrical Char	Per datasheet s	pec	Pass	Pass	Pass			
Wafer level Reliability	Approved	Pass	Pass	Pass				
Manufacturability (Assembly)	(per mfg. Site s	Pass	Pass	Pass				
Manufacturability (Wafer Fab)	(per mfg. Site s	Pass	Pass	Pass				
	evel 3-260C							
		e: SH6964BBA0G4						
	Wafer Fab Site: DMOS5 Wafer Fab Process: LBC7							
Qualification: Plan	Test Results							
Reliability Test	Conditions		Sample	Size (PAS	SS/FAIL)			
**Biased HAST	130C/85%RH (96 Hrs)		77/0	77/0	77/0			
Manufacturability (Wafer Fab)	ab) (per mfg. Site specification)			Pass				
Wafer level Reliability	Approved	Pass	Pass	Pass				
** Preconditioning sequence: Level 3-260C								

Qualification Device: SH6964BBA0G4							
Qualification Device: BQ24730RGF							
Wafer Fab Site: DMO	S5	S5 Wafer Fab Process					
Qualification: Plan	Test Results						
Reliability Test	Conditions		Sample Size (PASS/FAI		SS/FAIL)		
**Life Test 155C	240 Hrs		116/0	116/0	116/0		
Electrical Char	Per datasheet spec		Pass	Pass	Pass		
Manufacturability (Wafer Fab)	(per mfg. Site specification)		Pass				
Manufacturability (Assembly)	(per mfg. Site specification)		Pass				
Wafer level Reliability	Approved		Pass	Pass	Pass		
** Preconditioning sequence: Level 3-260C							

Addendum to:

5x6 QFN Q5MC Power Stage Qualification Summary NCH MOSFET - Gen 2.1 25-10

Second 42nd Fab Sourcing Qualification Summary (DMOS-5, UMC and Amkor-P3): CSD95372BQ5MC DMOS-5, UMC and Amkor-P3 Qualification Test Summary

Stress	Conditions	Test Duration	Sample Size	Results
HTOL	125°C/100%	1K hrs	3 lots x 77 units	Pass
	Rated Vin			

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com